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Modern Crystallography III

Crystal Growth

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With 244 Figures

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Contents

PART 1: CRYSTALLIZATION PROCESSES

(A.A. Chernov)

1	Equi	libriun	n	1
	$1.\overline{1}$		Equilibrium	
		1.1.1	One-Component Systems	1
			Multicomponent Systems	
		1.1.3	Crystallization Pressure	8
	1.2	Surfac	ce Energy and Periodic Bond Chains	9
			Surface Energy	9
		1.2.2	Periodic Bond Chains and Estimates of the Surface Energy	10
		1.2.3	Surface Energy Anisotropy	13
	1.3		ic Structure of the Surface	
		1.3.1	Surface Configurations and Their Energies	17
			Adsorption Layer	
			Step Roughness	
			Surface Roughness	
	1.4		Equilibrium with Allowance for Surface Energy.	
		Equili	brium Shape of a Crystal	37
			Phase Equilibrium over a Curved Surface	
		1.4.2	Equilibrium Shape of a Crystal	40
		1.4.3	Average Detachment Work. Finding Faces of Equilibrium	
			Shape	42
		1.4.4	Experimental Observation of an Equilibrium Shape	45
2	Nuc	leation	and Epitaxy	48
	2.1		ogeneous Nucleation	
		2.1.1	Work and Rate of Nucleation. Size and Shape of Nuclei	48
		2.1.2	Critical Supersaturation and Metastability Boundary in	
			Vapors	51
		2.1.3	Nucleation in Condensed Phases	54
		2.1.4	Transient Nucleation Processes	62
	2.2	Heter	ogeneous Nucleation	64
		2 2 1	Work and Rate of Nucleation Size and Shape of Nuclei	64

XVI	Contents

		2.2.2	Atomistic Picture of Nucleation. Clusters 70
			Decoration. Initial Stages of Growth
			Activity of Solid Surfaces in Melts 84
	2.3		xy
			Principal Manifestations
			Thermodynamics
			Kinetics
		2.3.4	Misfit Dislocations and the Conditions of Pseudomorphism 98
3	Grov	vth Me	echanisms
	3.1		al and Layer Growth of Crystals
	0.1		Conditions of Normal and Layer Growth
			Kinetic Coefficients in Normal Growth
			Layer Growth and the Anisotropy of the Surface Growth
		0.1.0	Rate
	3.2	Laver	Growth in Different Phases
		-	Growth from Vapor
			Growth from Solution
			Growth from the Melt
	3.3	Layer	Sources and Face Growth Rates
			Nuclei
		3.3.2	Dislocations
		3.3.3	Kinetic Coefficient and Anisotropy of Face Growth135
			Experimental Data on Layer Sources
	3.4	_	hology of a Surface Growing Layerwise
		3.4.1	Optical Methods Used to Investigate Growth Processes
			and Surfaces
		3.4.2	Steps, Vicinal Hillocks, and the Formation of Dislocations
			During Vapor Growth
			Kinematic Waves and Macrosteps
		3.4.4	Surface Melting
4	Imp	urities	
	4.1		t of Impurities on Growth Processes
			Thermodynamics and Structure of Solutions
		4.1.2	Adsorption
		4.1.3	Dependences of Growth and Morphology on the
	4.0	TC.	Concentration of Impurities
	4.2		oing of Impurities: Classification and Thermodynamics 169
			Classification
			Thermodynamics
		4.2.3	Equilibrium Impurity Distribution in a Crystal-Melt
			System

		4.2.4	Equilibrium Impurity Distribution in a Crystal-Solut		
			System	1	78
		4.2.5	Equilibrium in the Surface Layer	1	84
		4.2.6	Mutual Effects of Impurity Particles	1	85
	4.3	Trapp	ing of Impurities: Kinetics	1	87
		4.3.1	Surface Processes	1	87
			a) Statistical Selection	1	88
			b) Diffusional Relaxation	1	91
			c) Sectorial Structure	1	92
			d) Vicinal Sectoriality	1	93
			e) Rapid Diffusionless Crystallization		
		4.3.2	Pulse Annealing		
		4.3.3	Diffusion in the Mother Medium	2	02
			Observed Distribution Coefficients		
5	Mass	and H	leat Transport. Growth Shapes and Their Stability	2	80
	5.1	Mass a	and Heat Transfer in Crystallization	2	80
		5.1.1	Stagnant Solution. Kinetic and Diffusion Regimes.	2	09
		5.1.2	Stirred Solution. Summation of Resistances	2	11
		5.1.3	Kinetic and Diffusion Regimes in the Melt	2	13
		5.1.4	Diffusion Field of a Polyhedron	2	16
	5.2	Grow	th Shapes	2	19
		5.2.1	Kinematics	2	19
		5.2.2	Determination of Crystal Habit by the PBC Method	2	20
		5.2.3	The Bravais-Donnay-Harker Rule	2	23
		5.2.4	Effect of Growth Conditions	2	25
		5.2.5	Faceting Effect	2	28
	5.3	Stabil	ity of Growth Shapes	2	30
		5.3.1	Sphere	2	30
		5.3.2	Polyhedron	2	34
		5.3.3	Plane	2	40
6			f Defects		
	6.1	Inclus	sions	2	47
			Inclusions of the Mother Liquor		
			Inclusions of Foreign Particles		
	6.2	Dislo	cations, Internal Stresses and Grain Boundaries	2	56
		6.2.1	Dislocations from a Seed		
		6.2.2	Creation of Dislocations in Surface Processes	2	56
			Orientation of Dislocations		
		6.2.4	Thermal Stresses	2	60
		6.2.5	Dislocations Related to Vacancies and Impurities	2	73
		6.2.6	Grain Boundaries	2	76

XVIII	Contents
A V I I I	COHERINS

7	Mass 7.1 7.2 7.3 7.4 7.5	Solidi Geom Heat a Ripen	allization. fication Kinetics and Grain Size etric Selection and Ingot Formation and Mass Transfer ing (Coalescence) ples of Industrial Crystallization of Nonmetals.	279283285288
(E	.I. G		E GROWING OF CRYSTALS ov, K.S. Bagdasarov, V.A. Kuznetsov, L.N. Demianets, ev)	
8	Grov	wth fro	om the Vapor Phase	298
	8.1		riew	298
	8.2	The P	Physicochemical Bases of Crystallization from the	
			r Phase	300
		8.2.1	Surface Activity and the Preparation of Substrates and	
			Seeds	300
		8.2.2	Particle Flux Density in a Molecular Beam.	
			Concentration of the Substance in the Medium	302
		8.2.3	Structural Perfection of Crystals. Minimal, Maximal, and	
			Optimal Supersaturations. Epitaxial Temperature	303
			Heteroepitaxial Growth	
			Oriented Crystallization on Amorphous Substrates	
	8.3		cal Vapor Deposition	
			Molecular-Beam Method	
			Cathode Sputtering	
			Vapor Phase Crystallization in a Closed System	
			Gas Flow Crystallization	
	8.4		ical Vapor Deposition (CVD)	
			Chemical Transport	
			Vapor Decomposition Methods	
	0.5		Vapor-Synthesis Methods	
	8.5		nally Assisted Vapor Growth	
	8.6		allization from the Vapor via a Liquid Zone	343
		8.0.1	A General Description of the Vapor-Liquid-Solid	242
		063	Growth Mechanism (VLS)	
			Growth Kinetics by the VLS Process	345
		0.0.3	The VLS Mechanism and Basic Regularities in Whisker	

		8.6.4 Controlled Growth of Whiskers
9	Grow 9.1 9.2	th from Solutions
	9.3	c) Crystallization by Concentration-Induced Convection
		9.3.1 Methods of Growing Crystals from Hydrothermal Solutions
	9.4	9.3.5 Hydrothermal Growth of Crystals
10		th from the Melt

XX Contents

	10.1.1 State of the Melt	16
	10.1.2 Container Material4	19
	10.1.3 Crystallization Atmosphere	20
10.2	Principal Methods of Growing Single Crystals from the Melt .4	23
	10.2.1 Kyropoulos and Czochralski Methods	
	10.2.2 Stockbarger-Bridgman Method	29
	10.2.3 Verneuil Method	32
	10.2.4 Zone Melting	.36
	10.2.5 Heat Transfer in Crystal and Melt	40
	10.2.6 Temperature Control and Stabilization Systems 4	41
	10.2.7 The Automatic Control System for Growing Single	
	Crystals4	
	10.2.8 Choosing a Method for Crystal Growth4	45
10.3	Defects in Crystals Grown from the Melt and Ways to Control	
	the Real Structure of Grown Crystals	
	10.3.1 Foreign Inclusions	
	10.3.2 Impurities	
	10.3.3 Residual Stresses, Dislocations, and Grain Boundaries 4	-54
List of Sy	vmbols	ŀ56
Bibliogra	phy	62
Reference	es	ŀ67
Materials	Index	.95
Subject I	ndex	03